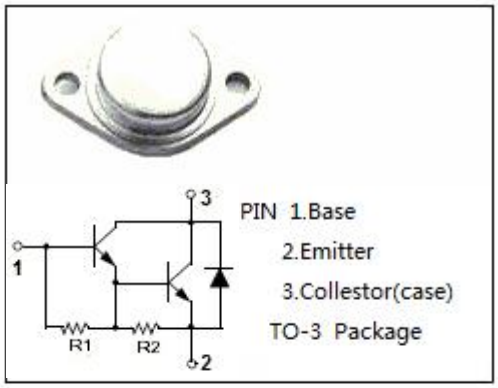
isc Silicon NPN Darlington Power Transistor 2N6492

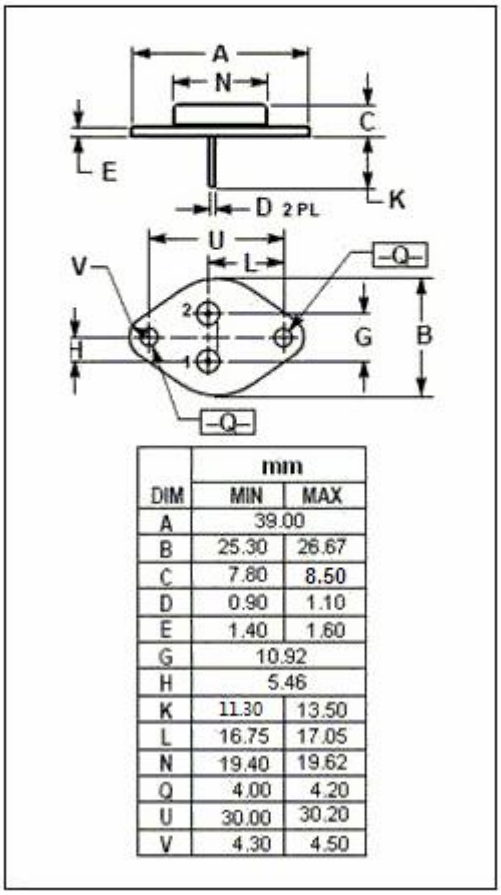
DESCRIPTION

- High DC current gain
  : h_{FE}= 500(Min)@ I_C= 3A
- With TO-3 package
- Low collector saturation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for general-purpose power amplifier and low frequency swithing applications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	55	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
P_C	Collector Power Dissipation@T_C=25℃	100	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.75	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ; I_B= 0	45			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=10A; I_B= 0.1A			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=10A; I_B= 0.1A			4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 3A ; V_{CE}= 4V			2.8	V
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			3	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 45V; I_B=0			1	mA
I_{CBO}	Collector Base Cutoff Current	V_{CB}=55V; I_E= 0			0.5	mA
h_{FE-1}	DC Current Gain	I_C= 3A; V_{CE}= 4V	500			
h_{FE-2}	DC Current Gain	I_C= 15A; V_{CE}= 4V	100			